

APPLICATION NO. 10/613586

January 28, 2005

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CLMPTO

1. (Currently Amended) A termination for a MOSgated device; said MOSgated device having an epitaxial junction-receiving layer of a given thickness; said epitaxial layer containing an active area and a termination area laterally adjacent said termination active area; said termination area including a bevel surface having a first edge adjacent to said active area and a second edge adjacent the outer edge of said device; ~~the surface of said bevel surface~~ coated with a resistive film for at least approximately linearly distributing the electric field within and along the termination area within said epitaxial layer.
2. (Original) The termination of claim 1, wherein said termination area has a lateral dimension which is about equal to or less than the thickness of said epitaxial layer.
3. (Original) The termination of claim 1, wherein said resistive film is of a material selected from the group consisting of nitrides, oxides, silicon carbide and semi-insulating films including amorphous silicon, sipos, and silicon-rich nitride.
4. (Original) The termination of claim 2, wherein said resistive film is of a material selected from the group consisting of nitrides, oxides, silicon carbide and semi-insulating films including amorphous silicon, sipos, and silicon-rich nitride.
5. (Original) The termination of claim 1, wherein said film is amorphous silicon.
6. (Original) The termination of claim 2, wherein said film is amorphous silicon.
7. (Original) The termination of claim 1, wherein said MOSgated device has a source electrode on its top surface and a drain electrode on its bottom surface; said resistive film connecting said source electrode to said drain electrode.

8. (Original) The termination of claim 2, wherein said MOSgated device has a source electrode on its top surface and a drain electrode on its bottom surface; said resistive film connecting said source electrode to said drain electrode.

9. (Original) The termination of claim 3, wherein said MOSgated device has a source electrode on its top surface and a drain electrode on its bottom surface; said resistive film connecting said source electrode to said drain electrode.

10. (Original) The termination of claim 6, wherein said MOSgated device has a source electrode on its top surface and a drain electrode on its bottom surface; said resistive film connecting said source electrode to said drain electrode.

CLAIMS 11-20 (CANCELLED)